

WITH ACCESS TO DIGITAL TEMPERATURE AND CORRECTED DIGITAL PRESSURE LOW-COST, FULLY AMPLIFIED, CALIBRATED, AND COMPENSATED IN A SINGLE PACKAGE AVAILABLE FOR DIFFERENTIAL, GAGE, & SINGLE-ENDED APPLICATIONS MULTIPLE PRESSURE RANGES AVAILABLE TO MEASURE PRESSURE DOWN TO 0.15 PSI FULL-SCALE AND UP TO 1.5 PSI FULL-SCALE

### DESCRIPTION

The Silicon Microstructures SM5852 series of OEM pressure sensors combines stateof-the-art pressure sensor technology with CMOS digital signal processing technology to produce an amplified, fully conditioned, multi-order pressure and temperature compensated sensor in a dual in-line package (DIP) configuration.

Combining the pressure sensor with a custom signal conditioning ASIC in a single package simplifies the use of advanced silicon micromachined pressure sensors. Now, the pressure sensor can be mounted directly to a standard printed circuit board and an amplified, high level, calibrated pressure signal can be acquired from the digital interface or analog output. This eliminates the need of additional circuitry. such as a compensation network or microcontroller containing a custom correction algorithm.

The **SM5852** Series pressure sensors are based on SMI's highly stable, piezoresistive pressure sensor chips mounted on a ceramic substrate. An electronically programmable ASIC is contained in the same package to provide calibration and temperature compensation.

The model **SM5852** is designed for operating pressure ranges from 0.15 PSI up to 1.5 PSI. For both models, the sensor output is ratiometric with the supply voltage.



### **FEATURES**

Amplified, calibrated, fully signal Conditioned output span of 4.0 VDC fullscale (0.5 to 4.5 V signal) Digital temperature and calibrated pressure available through I<sup>2</sup>C interface Output is ratiometric with supply voltage Multi-order correction for pressure nonlinearity (factory programmed) Multi-order correction for temperature coefficient of span and offset (factory programmed) Absolute, differential, gage, and single ended versions SMI's unique low-pressure die allows for a full-scale pressure range of 0-0.15 PSI

### TYPICAL APPLICATIONS

Barometric measurement Medical instrumentation Pneumatic control Gas flow Respirators and ventilators Heating, Ventilation and Air Conditioning (HVAC)

### THEORY OF OPERATION

The operation of the signal processor is depicted in the block diagram below. The external pressure sensor is a piezoresistive bridge. This transduces the applied pressure into an electronic signal, which feeds into the integrated amplifier of the ASIC.

During the amplification step an offset correction factor is added in order to allow maximum gain for a given pressure while minimizing the offset error.

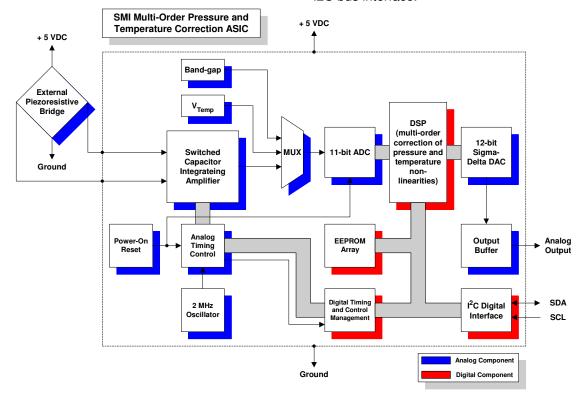
The signal is then passed to an 11-bit analog to digital converter (ADC). The ADC samples the signal multiple times and uses the sum of those samples as a 13-bit word.

A digital signal processor (DSP) is then used to correct and calibrate the pressure signal. The DSP provides multi-order correction of both pressure and temperature non-linearity through the use of factory-programmed

coefficients. A combined total of twenty coefficients are available for correcting pressure and temperature non-linearity. The unique coefficients are determined during a calibration process performed at the factory. Factory calibration is the last step performed which means the effect of the package on the pressure signal will also be taken into account. This provides a great advantage over conventional laser-trimming approaches.

The DSP outputs a corrected digital word, which travels to a 12-bit digital to analog converter (DAC) to provide a calibrated analog output. In addition to the analog output, the corrected pressure signal is accessible through an I<sup>2</sup>C digital interface.

See SMI application note AN05-001 for a detailed description of how to read out the digital corrected pressure signal using the I2C bus interface.



### CHARACTERISTICS FOR SM5852 – SPECIFICATIONS

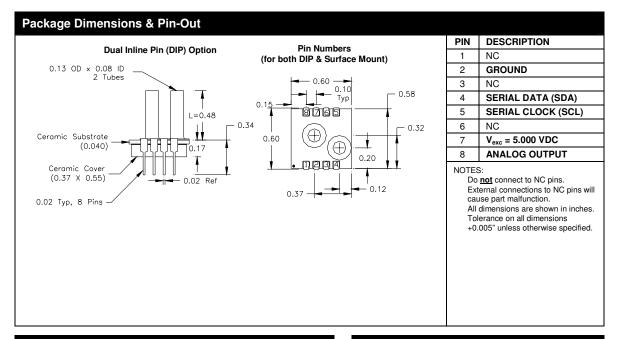
All parameters are measured at room temperature while applying 5.000V supply, unless otherwise specified.

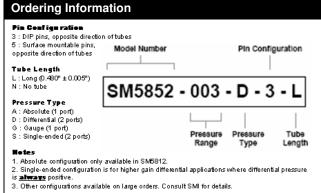
		Absolute <sup>1</sup> , Gage & Single <sup>2</sup>		<u>D</u> ifferential <sup>3</sup>					
		MIN	TYP	MAX	MIN	TYP	MAX	UNITS	NOTES
Zero output (gage)		0.42	0.50	0.58				V	4
Zero output (differential)					2.42	2.50	2.58	V	4
Output Span		3.92	4.00	4.08	1.96	2.00	2.04	V FS	4, 5, 6
	0.15 PSI	3.80	4.00	4.20	1.90	2.00	2.10	V FS	4, 5, 6
Linearity		-0.5		+0.5	-0.5		+0.5	%FS	6, 7
	0.15 PSI	-2.5		+2.5	-2.5		+2.5	%FS	6, 7
Pressure hysteresis	5812	-0.1		+0.1	-0.1		+0.1	%FS	8
	5852	-0.3		+0.3	-0.3		+0.3	%FS	8
Temperature coefficient - Zero		-1.0		+1.0	-1.0		+1.0	%FS	6
	0.15 PSI	-2.5		+2.5	-2.5		+2.5	%FS	6
Temperature coefficient – Span		-1.0		+1.0	-1.0		+1.0	%FS	6
	0.15 PSI	-2.0		+2.0	-2.0		+2.0	%FS	6
Thermal hysteresis		-0.1		+0.1	-0.1		+0.1	%FS	8
Response Time		2			2			msec	8
Supply voltage		4.75	5.00	5.25	4.75	5.00	5.25	V	4, 9
Current consumption				10			10	mA	6
Overpressure	5812	3X			3X			%FS	8, 10
	5852	15X			15X			%FS	8, 10
Operating temperature range		-40	25	+125	-40	25	+125	℃	8
Compensated temperature range		0	25	+75	0	25	+75	℃	11
Storage temperature range		-40	25	+125	-40	25	+125	℃	8
Media compatibility									8, 12
Weight			3			3		gram	8
Notes:	l l		•	•		•			

#### Notes:

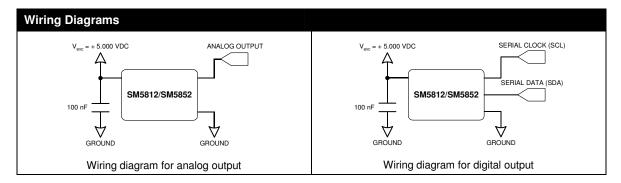
- 1. Absolute parts are only offered in the SM5812 Series.
- 2. Single-ended parts (Pressure Type S) have 2 ports and are for higher gain differential applications where the differential pressure is <u>always</u> positive.
- 3. Applies for positive pressure only.
- Sensor output is ratiometric to supply.
- 5. Full-scale (FS) is defined as zero pressure to rated pressure; differential parts can be used ±FS. Absolute and Gauge zero output is 0.5 V typical and full-scale output is 4.5 V. Span is the difference between Full-scale output and zero output, (4 V). For Differential parts, the negative full-scale is typically at 0.5 V, zero is typically 2.5 V, and positive full-scale is 4.5 V to give a span of ±2.0 V.
- 6. Tested on 100% of the parts.
- 7. Defined as best fit straight line for positive pressure applied to the part
- 8. Tested on a sample basis.
- 9. A 100 nF filter capacitor must be placed between Vsupply and Ground.
- Or 225 PSI, whichever is less. Output amplifier will saturate at about 0.25 V for applied pressure below the rated Zero and at about 4.75 V for applied pressure above the rated Full-scale.
- 11. Measured at 15 °C and 75 °C.
- Clean, dry gas compatible with wetted materials. Wetted materials include Pyrex glass, silicon, alumina ceramic, epoxy, RTV, gold, aluminum, and nickel.

## ADDITIONAL INFORMATION





Full-Scale Pressure Ranges										
SM5812	PSI	[kPa]	SM5852	PSI	[kPa]					
005	5	[34.5]	001	0.15	[1.0]					
015	15	[103.4]	003	0.30	[2.1]					
030	30	[206.8]	800	0.80	[5.5]					
060	60	[413.7]	015	1.50	[10.3]					
100	100	[689.5]	030	3.00	[20.7]					





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